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**IGBT** 

## SGH80N60UF

#### **Ultra-Fast IGBT**

#### **General Description**

Fairchild's UF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UF series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

#### **Features**

- · High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.1 \text{ V } @ I_C = 40 \text{A}$
- · High input impedance

#### **Applications**

AC & DC motor controls, general purpose inverters, robotics, and servo controls.





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description		SGH80N60UF	Units
V <sub>CES</sub>	Collector-Emitter Voltage		600	V
V <sub>GES</sub>	Gate-Emitter Voltage		± 20	V
	Collector Current	@ T <sub>C</sub> = 25°C	80	Α
IC	Collector Current	@ T <sub>C</sub> = 100°C	40	А
I <sub>CM (1)</sub>	Pulsed Collector Current		220	А
I <sub>F</sub>	Diode Continuous Forward Current	@ T <sub>C</sub> = 100°C	25	Α
I <sub>FM</sub>	Diode Maximum Forward Current		280	Α
$P_{D}$	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	195	W
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	78	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

**Notes:**(1) Repetitive rating: Pulse width limited by max. junction temperature

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.64	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Cha	racteristics					
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250uA$	600			V
$\Delta B_{VCES}/$ $\Delta T_{.1}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V$ , $I_C = 1mA$		0.6		V/°C
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			250	uA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			± 100	nA
On Cha	racteristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C = 40 \text{mA}, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
	Collector to Emitter	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V		2.1	2.6	V
V <sub>CE(sat)</sub>	Saturation Voltage	$I_C = 80A$ , $V_{GE} = 15V$		2.6		V
Dumami	- Chavastaviatias		•	•		
C <sub>ies</sub>	c Characteristics Input Capacitance			2790		ρF
	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$		350		PF
C <sub>oes</sub> C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz		100		pF
t <sub>d(on)</sub>	ng Characteristics Turn-On Delay Time			23		ns
t <sub>r</sub>	Rise Time			50		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_{C} = 40 \text{A},$		90	130	ns
t <sub>f</sub>	Fall Time	$R_G = 5\Omega$ , $V_{GE} = 15V$ ,		50	150	ns
Ė <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C		570		uJ
E <sub>off</sub>	Turn-Off Switching Loss			590		uJ
E <sub>ts</sub>	Total Switching Loss			1160	1500	uJ
t <sub>d(on)</sub>	Turn-On Delay Time			30		ns
t <sub>r</sub>	Rise Time			55		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_{C} = 40\text{A},$		150	200	ns
t <sub>f</sub>	Fall Time	$R_G = 5\Omega$ , $V_{GE} = 15V$ ,		160	250	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 125°C		630		uJ
E <sub>off</sub>	Turn-Off Switching Loss	1		940		uJ
E <sub>ts</sub>	Total Switching Loss	1		1580	2000	uJ
Q <sub>q</sub>	Total Gate Charge	V 200 V I 40A		175	250	nC
	Gate-Emitter Charge	$V_{CE} = 300 \text{ V}, I_{C} = 40 \text{A},$		25	40	nC
$Q_{ge}$	sate =ter snarge					
Q <sub>ge</sub> Q <sub>gc</sub>	Gate-Collector Charge	V <sub>GE</sub> = 15V		60	90	nC

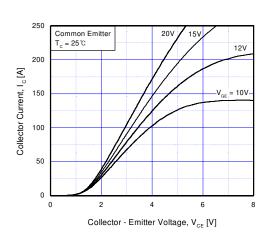


Fig 1. Typical Output Characteristics

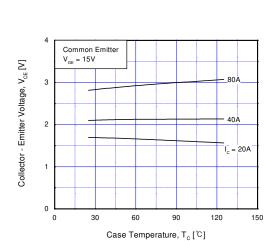


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

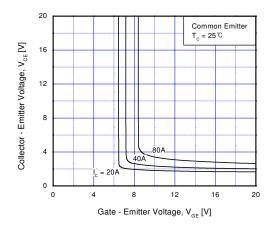


Fig 5. Saturation Voltage vs.  $V_{\text{GE}}$ 

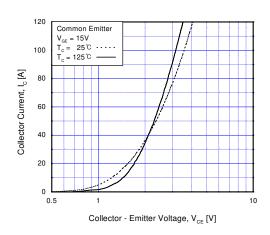


Fig 2. Typical Saturation Voltage Characteristics

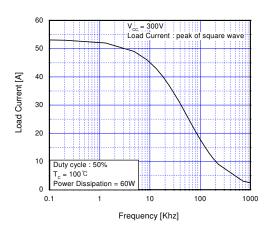


Fig 4. Load Current vs. Frequency

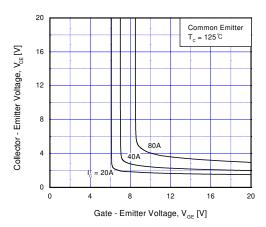


Fig 6. Saturation Voltage vs.  $V_{\rm GE}$ 

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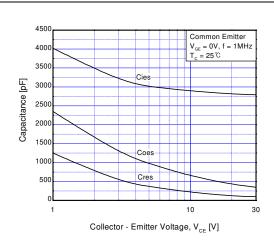
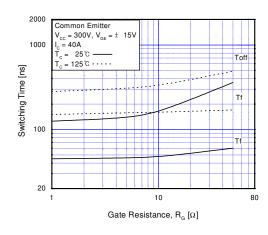


Fig 7. Capacitance Characteristics

Fig 8. Turn-On Characteristics vs.
Gate Resistance



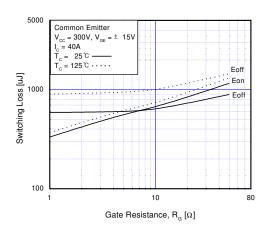
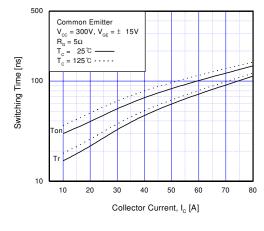


Fig 9. Turn-Off Characteristics vs.
Gate Resistance

Fig 10. Switching Loss vs. Gate Resistance



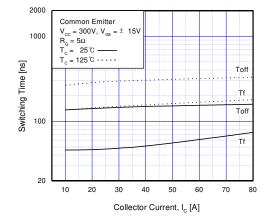
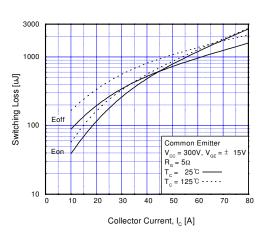


Fig 11. Turn-On Characteristics vs. Collector Current

Fig 12. Turn-Off Characteristics vs. Collector Current



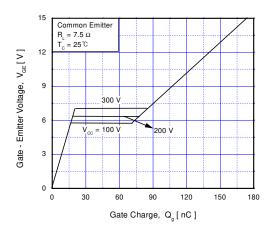
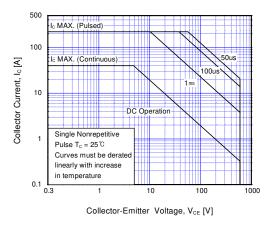


Fig 13. Switching Loss vs. Collector Current

Fig 14. Gate Charge Characteristics



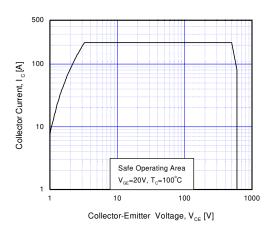


Fig 15. SOA Characteristics

Fig 16. Turn-Off SOA Characteristics

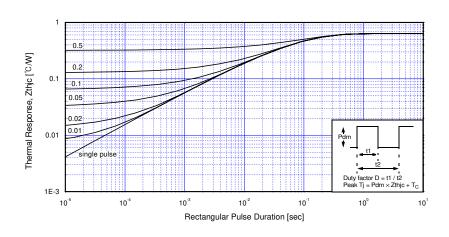
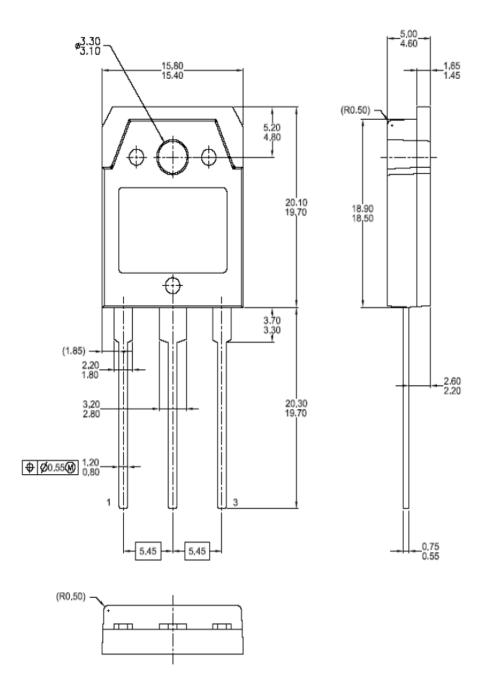


Fig 17. Transient Thermal Impedance of IGBT



## TO-3PN



Dimensions in Millimeters

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